

LL41

$V_{RRM} : 100V$

FEATURES :

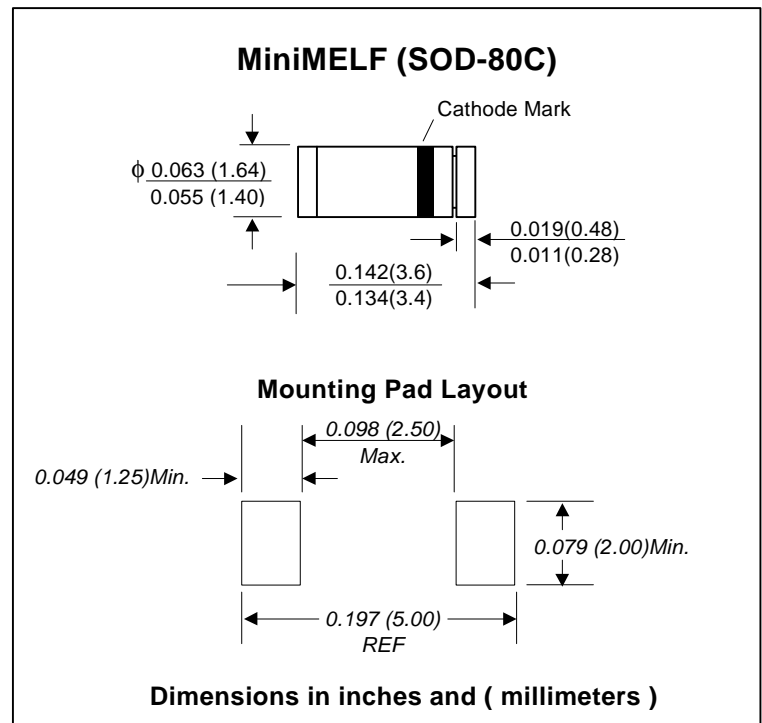
- For general purpose applications
- This diode features low turn-on voltage and high breakdown voltage. This device is protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges
- This diode is also available in the DO-35 case with type designation BAT41.

MECHANICAL DATA :

Case: MiniMELF Glass Case (SOD-80C)

Weight: approx. 0.05g

SCHOTTKY BARRIER DIODE



Maximum Ratings and Thermal Characteristics (Rating at 25 °C ambient temperature unless otherwise specified.)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	100	V
Continuous Forward Current	I_F	100 ⁽¹⁾	mA
Repetitive Peak Forward Current at $t_p < 1s$	I_{FRM}	350 ⁽¹⁾	mA
Forward Surge Current at $t_p = 10 ms$,	I_{FSM}	750 ⁽¹⁾	mA
Power Dissipation	PD	400 ⁽¹⁾	W
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	300 ⁽¹⁾	°C/W
Junction Temperature	T_J	125	°C
Ambient Operating Temperature Range	T_a	-65 to + 125	°C
Storage temperature range	T_s	-65 to + 150	°C

Electrical Characteristics ($T_J = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Breakdown Voltage ⁽²⁾	$V_{(BR)R}$	$I_R = 100 \mu A$	100	110	-	V
Reverse Current ⁽²⁾	I_R	$V_R = 50 V$	-	-	100	nA
		$V_R = 50 V, T_J = 100^\circ C$	-	-	20	μA
Forward Voltage ⁽²⁾	V_F	$I_F = 1mA$	-	0.4	0.45	V
		$I_F = 200mA$	-	-	1.0	
Diode Capacitance	Cd	$V_R = 1 V, f = 1MHz$	-	2	-	pF
Reverse Recovery Time	T_{rr}	$I_F = 10mA, I_R = 10mA,$ to $I_R = 1mA, R_L = 100\Omega$	-	5	-	ns

Note: (1) Valid provided that electrodes are kept at ambient temperature

(2) Pulse test, $t_p = 300\mu s$